

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:	)	PATENT APPLICATION
	)	
Inventors: Fengyan Zhang and Sheng Teng Hsu	)	
	)	
Serial No.: Not Yet Assigned	)	Attorney Docket No.
	)	SLA 0804
Filed: Herewith	)	
	)	
Title: ONE MASK P/PCMO/Pt STACK ETCHING PROCESS FOR RRAM APPLICATIONS	)	
	)	

Honorable Commissioner for Patents  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97**

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by the Examiner and made of record in the above-identified application.

(Date)

9/30/03

Respectfully submitted,

David C. Ripma  
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<b>1449A/PTO</b> Rev. 10/95		<b>U.S. Department of Commerce</b> Patent and Trademark Office		<b>Complete If Known</b>	
				Application Number	
				Filing Date	September 30, 2003
				First Named Inventor	Fengyan Zhang
				Group Art Unit	
				Examiner Name	
<b>LIST OF PRIOR ART CITED BY APPLICANT</b>  (use as many sheets as necessary)				Attorney Docket No.	SLA.0804
Sheet	1	of	1		

<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document Kind Number Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear

<b>FOREIGN PATENT DOCUMENTS</b>								
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear	T <sup>6</sup>
		Office <sup>3</sup> Code <sup>5</sup>	Number <sup>4</sup>	Kind				

<b>OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS</b>			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T <sup>2</sup>
		Lee et al., Dry Etching to Form Submicron Features in CMR Oxides: PrBaCaMnO <sub>3</sub> and LaSr MnO <sub>3</sub> , <a href="http://mse.ufl.edu/~spear/recent_papers/cmr_oxides/cmr_oxides.pdf">http://mse.ufl.edu/~spear/recent_papers/cmr_oxides/cmr_oxides.pdf</a>	

Examiner Signature		Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.  
<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1<sup>6</sup> if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached